

SOT223 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

Product Summary

V _{(BR)DSS}	Max R _{DS(on)}	Max I _D T _A = +25°C
60V	$1\Omega @ V_{GS} = 10V$	1A

Features and Benefits

- Repetitive avalanche rating
- No transient protection required
- Characterized for 5V logic drive
- Lead-Free Finish; RoHS Compliant (Notes 1& 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

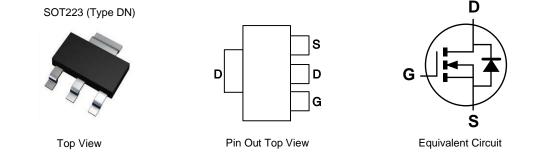
Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for highefficiency power management applications.

- Automotive relay drivers
- Stepper motor drivers

Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)



Ordering Information (Note 4)

Part Number	Package	Part Number Package		Packing	
Fart Nulliger	Гаскауе	Qty.	Carrier		
ZVN4206GVTA	SOT223 (Type DN)	1,000	Tape & Reel		

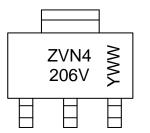
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\label{eq:2VN4206V} \begin{array}{l} \mathsf{ZVN4206V} = \mathsf{Product Type Marking Code} \\ \mathsf{YWW} = \mathsf{Date Code Marking} \\ \mathsf{Y \ or } \overline{\mathsf{Y}} = \mathsf{Last Digit of Year (ex: 1= 2021)} \\ \mathsf{WW \ or } \overline{\mathsf{WW}} = \mathsf{Week Code (01~53)} \end{array}$



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	ID	1	A
Pulsed Drain Current	I _{DM}	8	A
Continuous Drain Current	ID	1	A
Continuous Body Diode Current	I _{SD}	600	mA
Avalanche Current - Repetitive	I _{AR}	600	mA
Avalanche Energy - Repetitive	E _{AR}	15	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C	P _{tot}	2	W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

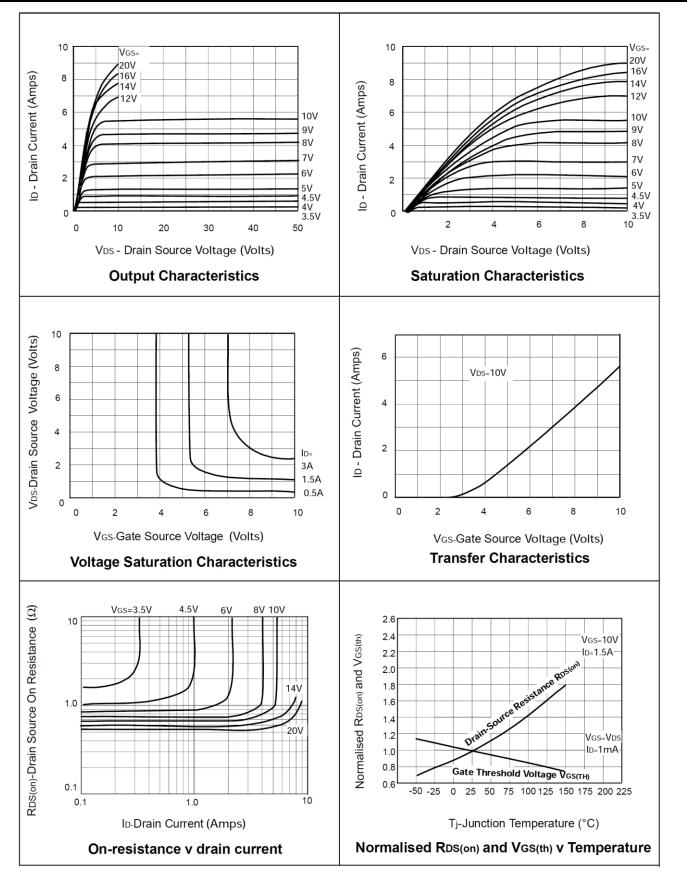
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	_	V	$I_D = 1mA$, $V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	10 100	μA	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 48V, V_{GS} = 0V, T=+125^{\circ}C$ (Note 6)	
Gate-Body Leakage	I _{GSS}	—	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate-Source Threshold Voltage	V _{GS(th)}	1.3	_	3	V	$I_D = 1mA$, $V_{DS} = V_{GS}$	
On-State Drain Current (Note 5)	I _{D(on)}	3	_	_	А	$V_{DS} = 25V, V_{GS} = 10V$	
Static Drain-Source On-State Resistance (Note 5)		_	—	1	Ω	V _{GS} = 10V, I _D = 1.5A	
Static Drain-Source On-State Resistance (Note 5)	R _{DS} (ON)	_	_	1.5		$V_{GS} = 5V, I_D = 0.5A$	
Forward Transconductance (Notes 5 & 6)	g _{fs}	300	_		ms	V _{DS} = 25V, I _D = 1.5A	
DYNAMIC CHARACTERISTICS						·	
Input Capacitance (Note 6)	Ciss	—	_	100	pF	V _{DS} = 25 V, V _{GS} = 0V f = 1MHz	
Output Capacitance (Note 6)	Coss	—	-	60	pF		
Reverse Transfer Capacitance (Note 6)	Crss	_	—	20	pF		
Turn-On Delay Time (Notes 6 & 7)	t _{d(on)}	_	—	8	ns	V _{DD} ≈ 25V, V _{GEN} = 10V I _D = 1.5A	
Turn-On Rise Time (Notes 6 & 7)	tr		—	12	ns		
Turn-Off Delay Time (Notes 6 & 7)	t _{d(off)}		—	12	ns		
Turn-Off Fall Time (Notes 6 & 7)	t _f	—	—	15	ns		

Notes: 5. Measured under pulsed conditions. Width=300 μ s. Duty cycle \leq 2%.

6. Sample test. 7. Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator.

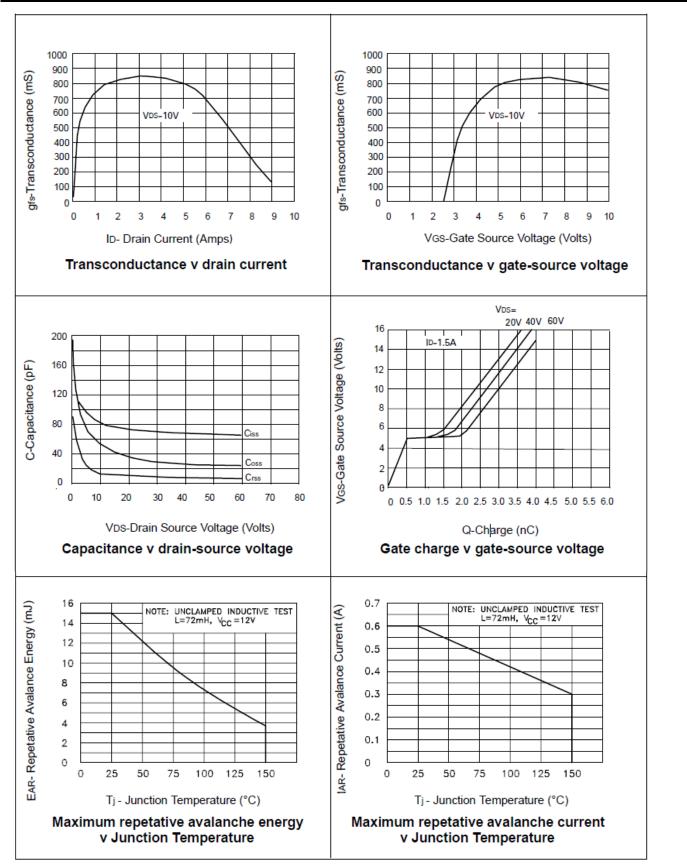


Typical Characteristics





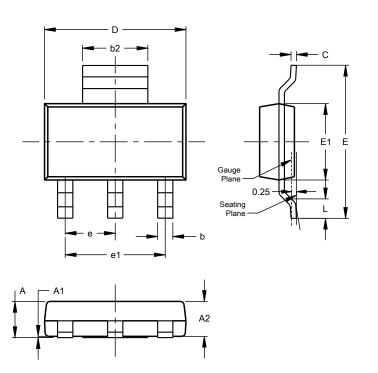
Typical Characteristics (continued)





Package Outline Dimensions

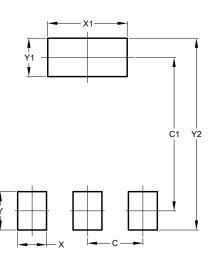
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223 (Type DN)				
Dim	Min	Max	Тур	
Α		1.70		
A1	0.01	0.15		
A2	1.50	1.68	1.60	
b	0.60	0.80	0.70	
b2	2.90	3.10		
С	0.20	0.32		
D	6.30	6.70		
E	6.70	7.30		
E1	3.30	3.70		
е			2.30	
e1			4.60	
L	0.85			
All [All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223 (Type DN)

Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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